

Peak Sensitivity Wavelength: 950nm

The MTD5032M8 is a photo diode in a metal can package. It is well suited for high reliability and high speed applications.

FEATURES

- > Ultra High Speed
- > Low Dark Current / Metal Can Package
- > Wide Angular Response
- > Active Area: 17.7mm²

APPLICATIONS

- > Optical Switches
- > Edge Sensing
- > Smoke Detectors



Absolute Maximum Ratings (Ta=25°C)



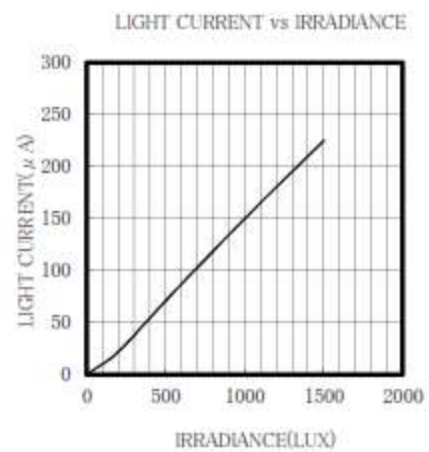
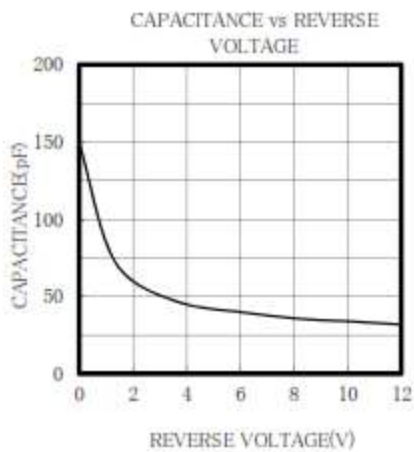
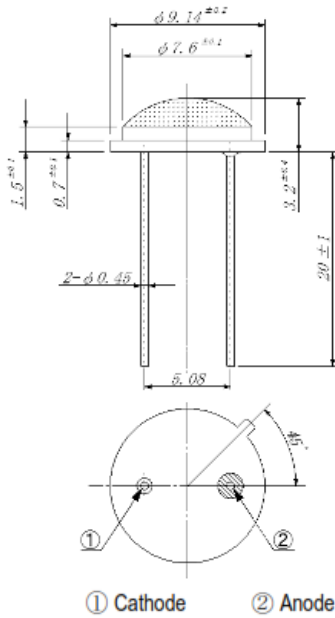
ITEMS	SYMBOL	RATINGS	UNIT
Reverse Voltage	VR	30	V
Power Dissipation	PD	100	mW
Operating Temperature Range	Topr	-25 ~ +100	°C
Storage Temperature Range	Tstg	-30 ~ +125	°C
Lead Soldering Temperature*1	Tls	260	°C

*1: Time 5 Sec max, Position: Up to 3mm from the body.

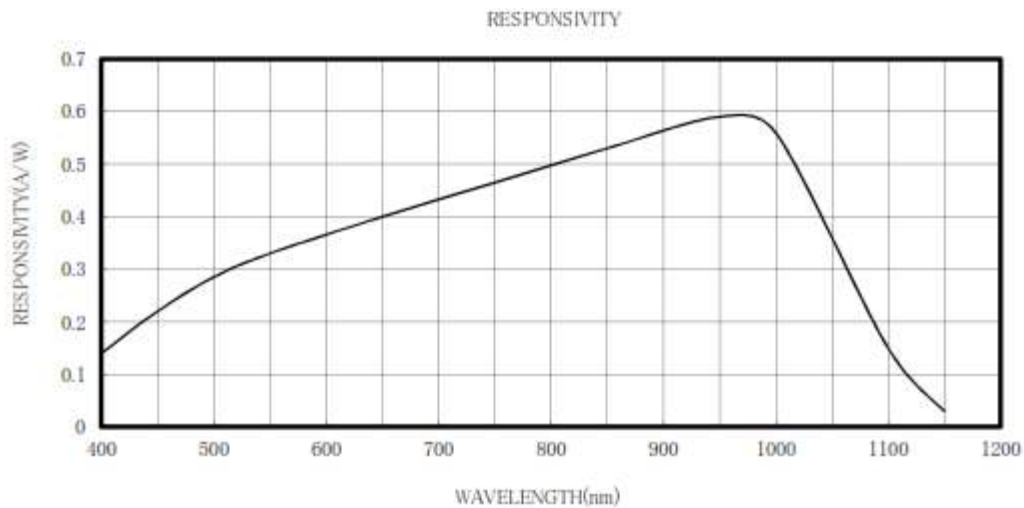
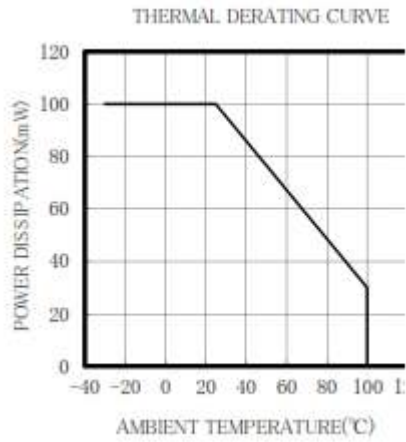
Electrical & Optical Characteristics (Ta = 25°C)

ITEMS	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Light Current	IL	VR= 10V,L= 1000Lux	--	150	--	μA
Dark Current	ID	VR=10V	--	--	10	nA
Spectral Sensitivity	λ	--	--	400~1100	--	nm
Peak Sensitivity Wavelength	λp	--	--	950	--	nm
Switching Time (Rise Time)	Tr	RL=50Ω, Vr=0V	--	--	100	nS
Switching Time (Fall Time)	Tf	RL=50Ω, Vr=0V	--	--	100	nS
Junction Capacitance	Cj	VR= 10V	--	--	50	pF

* Color Temperature=2870°K Standard Tungsten Lamp



Unit: mm, Tolerance: ± 0.2



The information contained herein is subject to change without notice.

2025-04-09